

## Product Overview

### 1N5819: Schottky Barrier Rectifier, 1.0 A, 40 V

For complete documentation, see the data sheet.

The Schottky Rectifier employs the Schottky Barrier principle in a large area metal-to-silicon power diode. The Schottky Rectifier's state-of-the-art geometry features chrome barrier metal, epitaxial construction with oxide passivation and metal overlap contact. It is ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes and polarity protection diodes.

### Features

- Extremely Low  $v_F$
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency Mechanical Characteristics
- Case: Epoxy, Molded
- Weight: 0.4 gram (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Shipped in plastic bags, 1000 per bag.
- Available Tape and Reeled, 5000 per reel, by adding a "RL" suffix to the part number
- Polarity: Cathode Indicated by Polarity Band
- Marking: 1N5817, 1N5818, 1N5819

For more features, see the data sheet

### Part Electrical Specifications

Product	Compliance	Status	Configuration	$V_{RRM}$ Min (V)	$V_F$ Max (V)	$I_{RM}$ Max ( $\mu$ A)	$I_{O(ree)}$ Max (A)	$I_{FSM}$ Max (A)	$t_r$ Max (ns)	$C_j$ Max (pF)	Package Type
1N5819	Pb-free	Active	Single	40	0.6	1000	1	25	-	-	Axial Lead / DO-41
1N5819G	Pb-free Halide free	Active	Single	40	0.6	1000	1	25	-	-	Axial Lead-2
1N5819RLG	Pb-free Halide free	Active	Single	40	0.6	1000	1	25	-	-	Axial Lead-2

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

Created on: 9/23/2019